Silicon NPN Power Transistors 2SD627

DESCRIPTION

·With TO-3 package

·High voltage,high speed

APPLICATIONS

·For use in horizontal deflection output stages for color TV receivers

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		3	A
I_{CM}	Collector current-peak		6	A
P_C	Collector power dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-45~150	□

Silicon NPN Power Transistors 2SD627

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ;I_B=0	600			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2.5A; I_B=0.6A			10	V
V_{BEsat}	Base-emitter saturation voltage	I_C=2.5A; I_B=0.6A			1.6	V
I_{CBO}	Collector cut-off current	V_{CB}=1000V; I_E=0			50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			1.0	mA
h_{FE}	DC current gain	I_C=2A ; V_{CE}=10V	5		25	
t_f	Fall time	I_{CP}=2.5A			1.0	μs

PACKAGE OUTLINE

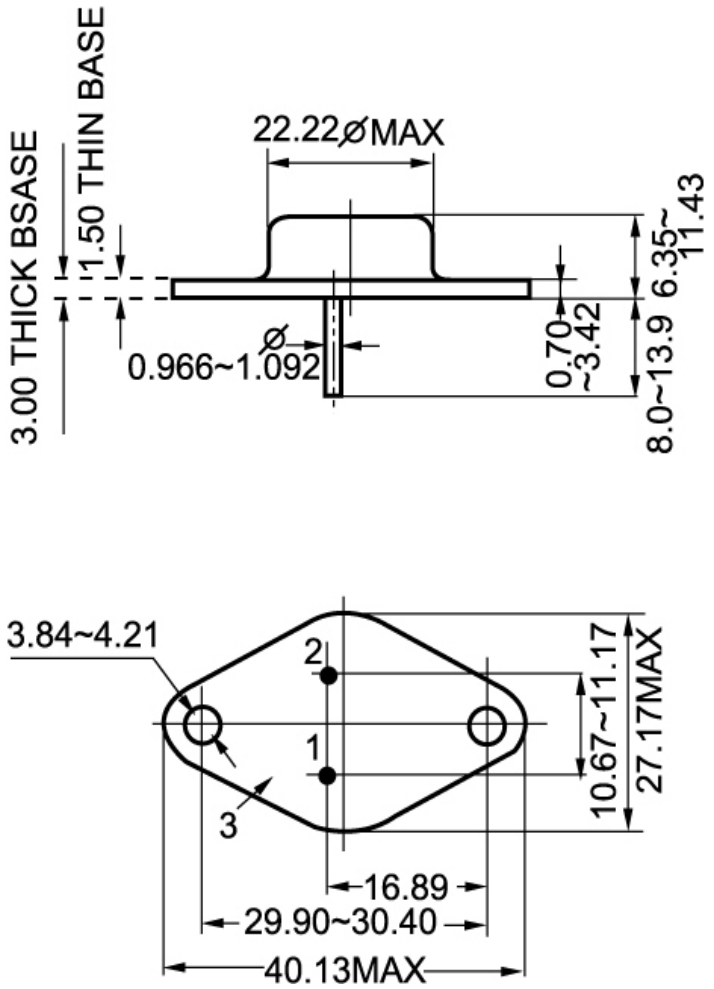

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)